Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (currently amended) A fabricating method of a semiconductor device comprising:
- (a) forming a film which to form a pattern on a structure of a semiconductor substrate;
- (b) forming an anti-reflection layer on the film to form a stacking structure including the film and the anti-reflection layer;
- (c) performing a plasma treatment to form a plurality of adjacent grooves on an upper surface of the stacking structure, wherein the grooves are configured to increase adhesion between the upper surface of the stacking structure and a photoresist layer;
- (d) forming a photoresist pattern on the stacking structure on which the grooves are formed; and
- (e) etching the stacking structure using the photoresist pattern as a mask to form a stacking structure pattern.
- 2. (original) The method of claim 1, wherein performing the plasma treatment includes performing the plasma treatment for 15-30 seconds using N₂O plasma.

- 3. (currently amended) The method of claim 1, wherein forming the photoresist [[patterin]] <u>pattern</u> includes applying a photoresist layer, exposing the photoresist layer to a light selectively, and developing the photoresist layer to form the photoresist pattern exposing a part of the stacking structure.
- 4. (original) The method of claim 3, wherein a far ultraviolet ray is used as a light source in exposing the photoresist layer to a light selectively.
- 5. (original) The method of claim 1, wherein a SiO_xN_y layer having thickness of 200~300Å is used as the anti-reflection layer.
 - 6. (original) The method of claim 1, wherein the film is a metal film.
- 7. (original) The method of claim 1, wherein forming the antireflection layer includes forming a protective oxide layer on the anti-reflection layer after forming the anti-reflection layer to form a stacking structure including the film, the anti-reflection layer, and the protective oxide layer.
- 8. (original) The method of claim 7, wherein the protective oxide layer is formed to have thickness of equal to or less than 100Å.
- 9. (original) The method of claim 7, wherein the plasma treatment is performed for 15-30 seconds using N_2O plasma.

- 10. (original) The method of claim 7, wherein a SiO_xN_y layer having thickness of 200~300Å is used as the anti-reflection layer.
 - 11. (original) The method of claim 7, wherein the film is a metal film.

Claims 12-20 (canceled)

- 21. (new) A fabricating method of a semiconductor device comprising:
- (a) forming a film which to form a pattern on a structure of a semiconductor substrate;
 - (b) forming an anti-reflection layer on the film;
- (c) forming a protective oxide layer on the anti-reflection layer after forming the anti-reflection layer to form a stacking structure including the film, the anti-reflection layer, and the protective oxide layer;
- (d) performing a plasma treatment to form grooves on an upper surface of the stacking structure;
- (e) forming a photoresist pattern on the stacking structure on which the grooves are formed; and
- (f) etching the stacking structure using the photoresist pattern as a mask to form a stacking structure pattern.
- 22. (new) The method of claim 21, wherein the protective oxide layer is formed to have thickness of equal to or less than 100Å.

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- 23. (new) The method of claim 21, wherein the plasma treatment is performed for 15-30 seconds using N_2O plasma.
- 24. (new) The method of claim 21, wherein a SiO_xN_y layer having thickness of 200~300Å is used as the anti-reflection layer.
 - 25. (new) The method of claim 21, wherein the film is a metal film.

Amendments to the Drawings:

The attached replacement sheet of drawing includes changes to FIG. 1. This replacement sheet, which includes FIGS. 1 and 2, replaces the original sheet including FIGS. 1 and 2. The attached annotated sheet shows changes to FIG. 1 in red ink. In amended FIG. 1, the previously omitted descriptive legend "(Prior Art)" has been added.

Attachment: Replacement Sheet

Annotated Sheet Showing Changes